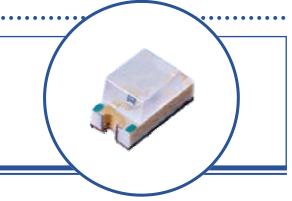
# Infrared Light Emitting Diode in Miniature SMD Package





- Flat Lens
- High Power
- 0805 Package Size
- 880nm Wavelength



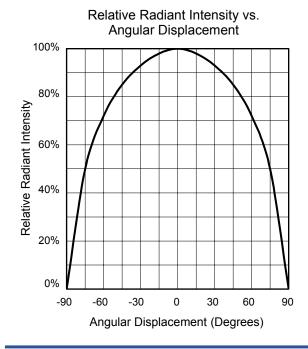
## PRELIMINARY

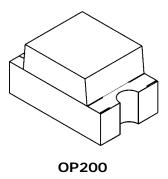
The OP200 is a GaAlAs infrared LEDs mounted in a miniature SMT package. The device incorporates a flat molded lens which enables a wide beam angle and provides an even emission pattern. This device is packaged in a 0805 size chip carrier that is compatible with most automated mounting equipment. The OP200 is mechanically and spectrally matched to the OP520 series phototransistors.

#### **Applications**

- Non-Contact Position Sensing
- Datum detection

- Machine automation
- Optical encoders









## SMD Infrared LED **OP200**



# Absolute Maximum Ratings T<sub>A</sub> = 25° C unless otherwise noted

Storage Temperature Range	-40° C to +85° C
Operating Temperature Range	-25° C to +85° C
Lead Soldering Temperature	260° C <sup>(1)</sup>
Reverse Voltage	30 V
Continuous Forward Current	50 mA
Power Dissipation	130 mW <sup>(2)</sup>

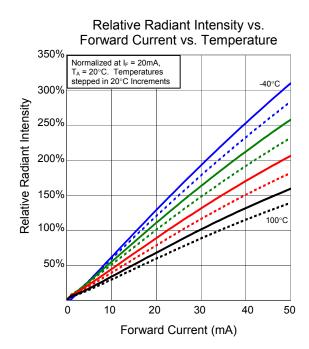
#### Notes:

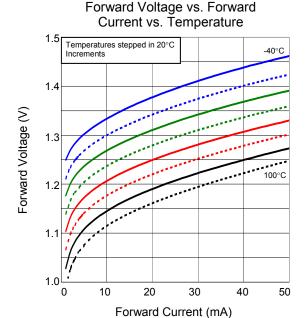
- Solder time less than 5 seconds at temperature extreme.
- De-rate linearly at 2.17 mW/° C above 25° C.

### Electrical Characteristics (T<sub>A</sub> = 25°C unless otherwise noted)

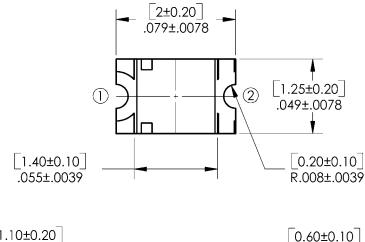
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	CONDITIONS
E <sub>e(APT)</sub>	Apertured Radiant Incidence	0.2			mW/cm <sup>2</sup>	I <sub>F</sub> = 20mA <sup>(3)</sup>
V <sub>F</sub>	Forward Voltage			1.5	V	I <sub>F</sub> = 20mA
I <sub>R</sub>	Reverse Current			100	μΑ	V <sub>R</sub> = 2.0V
$\lambda_{P}$	Peak Emission Wavelength		890		nm	I <sub>F</sub> = 10mA
$\Theta_{HP}$	Emission Angle at Half Power Points		150		Deg.	I <sub>F</sub> = 20mA
t <sub>r</sub> , t <sub>f</sub>	Rise and Fall Time			500	ns	$I_{F(PEAK)}$ = 100mA, PW = 10 $\mu$ s, 10% D.C.

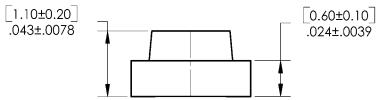
 $E_{e(APT)}$  is a measurement of the apertured radiant incidence upon a sensing area 0.081" (2.06mm) in diameter, perpendicular to and centered on the mechanical axis of the lens, and 0.590" (14.99mm) from the measurement surface.  $E_{e(APT)}$  is not necessarily uniform within the measured area.

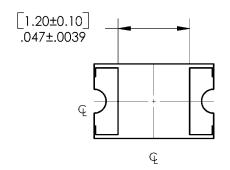












PIN	FUNCTION			
1	Anode			
2	Cathode			

DIMENSIONS ARE IN INCHES AND [MILLIMETERS].